

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

2SK3747 — High-Voltage, High-Speed Switching Applications

Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching
- High reliability (Adoption of HVP process)
- · Attachment workability is good by Mica-less package
- · Avalanche resistance guarantee

Specifications

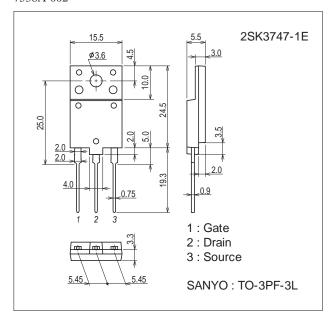
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		1500	V
Gate-to-Source Voltage	VGSS		±35	V
Drain Current (DC)	ID		2	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	4	А
Allowable Power Dissipation	D=		3.0	W
	PD	Tc=25°C	50	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		41	mJ
Avalanche Current *2	I _{AV}		2	Α

Note :*1 V_{DD} =50V, L=20mH, I_{AV} =2A (Fig.1)

Package Dimensions

unit : mm (typ) 7538A-002



Product & Package Information

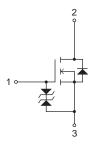
Package : TO-3PF-3L
JEITA, JEDEC : SC-94

• Minimum Packing Quantity: 30 pcs./magazine

Marking

Electrical Connection





^{*2} L≤20mH, single pulse

Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions	Ratings			Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	1500			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1200V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.5		3.5	V
Forward Transfer Admittance	yfs	V _{DS} =20V, I _D =1A	0.7	1.4		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =1A, V _G S=10V		10	13	Ω
Input Capacitance	Ciss			380		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		70		pF
Reverse Transfer Capacitance	Crss			40		рF
Turn-ON Delay Time	t _d (on)			12		ns
Rise Time	tr	See Fig 2		37		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		152		ns
Fall Time	tf			59		ns
Total Gate Charge	Qg			37.5		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =2A		2.7		nC
Gate-to-Drain "Miller" Charge	Qgd			20		nC
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0V		0.88	1.2	V

Fig.1 Avalanche Resistance Test Circuit

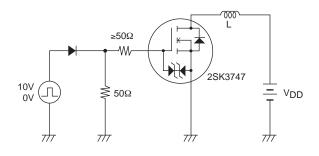
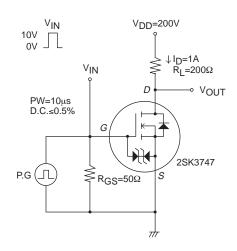
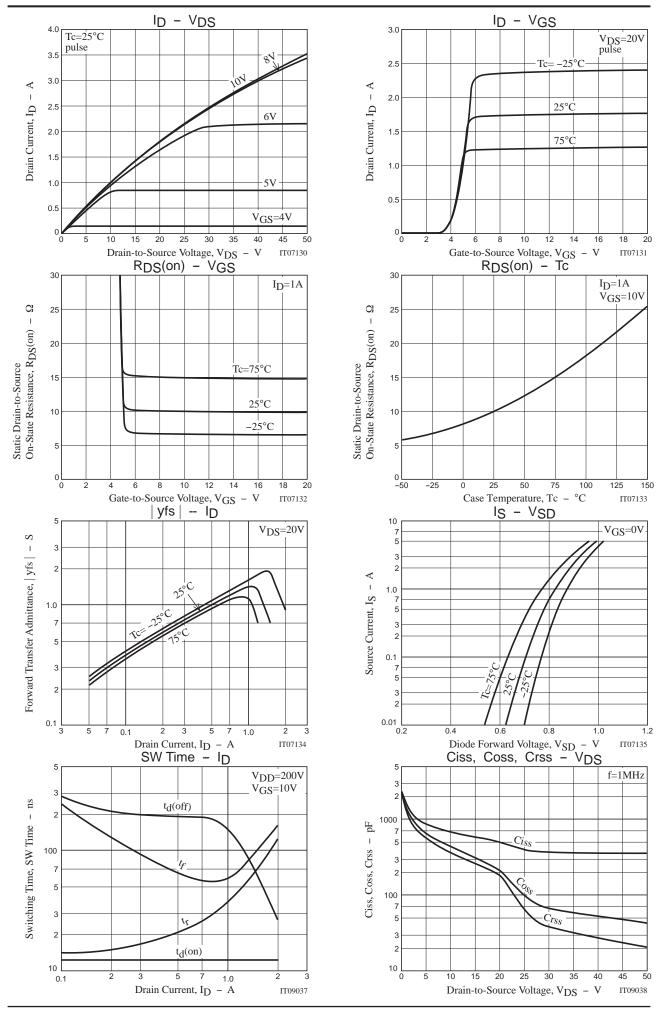


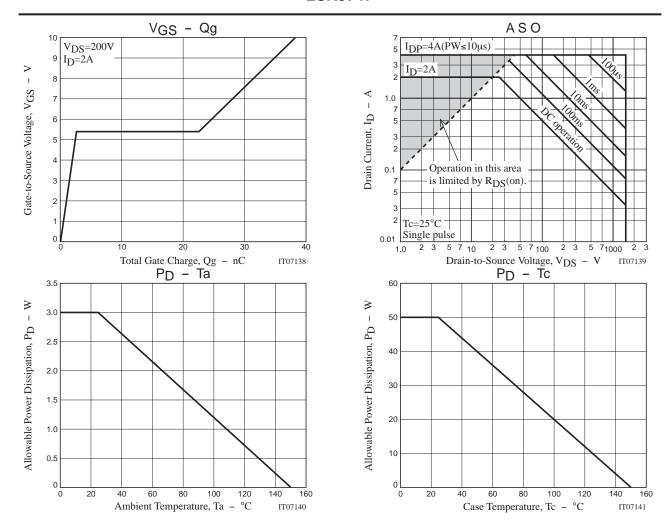
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo	
2SK3747-1E	TO-3PF-3L	30pcs./magazine	Pb Free	



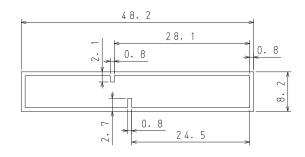


Magazine Specification

2SK3747-1E

1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			Packing format		
I dona 80 Mamo	Magazine Inner box Outer box		Outer box	Inner BOX	Outer BOX	
TO-3PF-3L	30	360	1440	12 magazines contained	SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590x225x178	



Tolerance=±0.2mm
Thickness=0.8±0.2mm
Length =508.0±1mm
Material =PVC or PET
(Antistatic treatment)

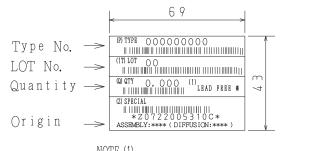
3. Storage method to magazine

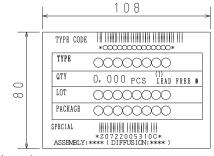


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



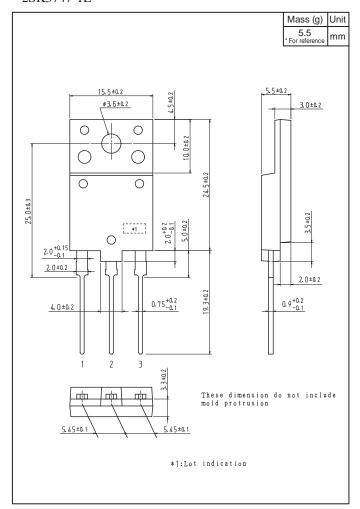


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase			
LEAD FRE	E 3	JEITA Phase 3A			

Outline Drawing

2SK3747-1E



Note on usage: Since the 2SK3747 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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